Unit: mm

TOSHIBA Diode Silicon Epitaxial Planar Type

HN1D03F

Ultra High Speed Switching Application

• Built in anode common and cathode common.

Unit 1

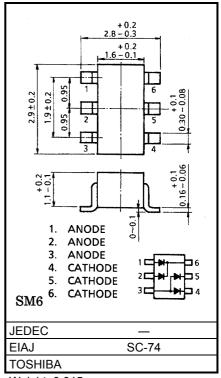
- Low forward voltage Q1, Q2: $V_{F(3)} = 0.90V$ (typ.)
- Fast reverse recovery time Q1, Q2: $t_{rr} = 1.6ns$ (typ.)
- Small total capacitance $Q1, Q2: C_T = 0.9 pF (typ.)$

Unit 2

- Low forward voltage Q3, Q4: $V_{F(3)} = 0.92V$ (typ.)
- Fast reverse recovery time Q3, Q4: trr = 1.6ns (typ.)
- Small total capacitance Q3, Q4: CT = 2.2pF (typ.)



Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V _{RM}	85	V
Reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300 (*)	mA
Average forward current	Ι _Ο	100 (*)	mA
Surge current (10ms)	I _{FSM}	2 (*)	А
Power dissipation	Р	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

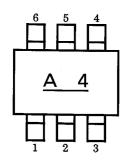


Weight: 0.015g

(*) This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4). In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.

Marking

Pin Assignment (Top View)



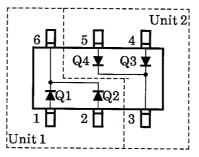
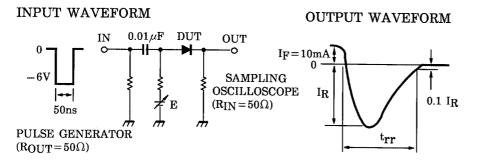


Fig.1 Reverse Recovery Time (t_{rr}) Test Circuit



Unit 1 Electrical Characteristics (Q1, Q2, Common) (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V _{F (1)}	_	I _F = 1mA		0.60		
	V _{F (2)}	-	I _F = 10mA		0.72		V
	V _{F (3)}	-	I _F = 100mA		0.90	1.20	
Reverse current	I _{R (1)}	-	V _R = 30V	_	—	0.1	μΑ
	I _{R (2)}	_	V _R = 80V	-	_	0.5	
Total capacitance	CT	_	V _R = 0, f = 1MHz		0.9	3.0	pF
Reverse recovery time	t _{rr}	_	I _F = 10mA (fig.1)	_	1.6	4.0	ns

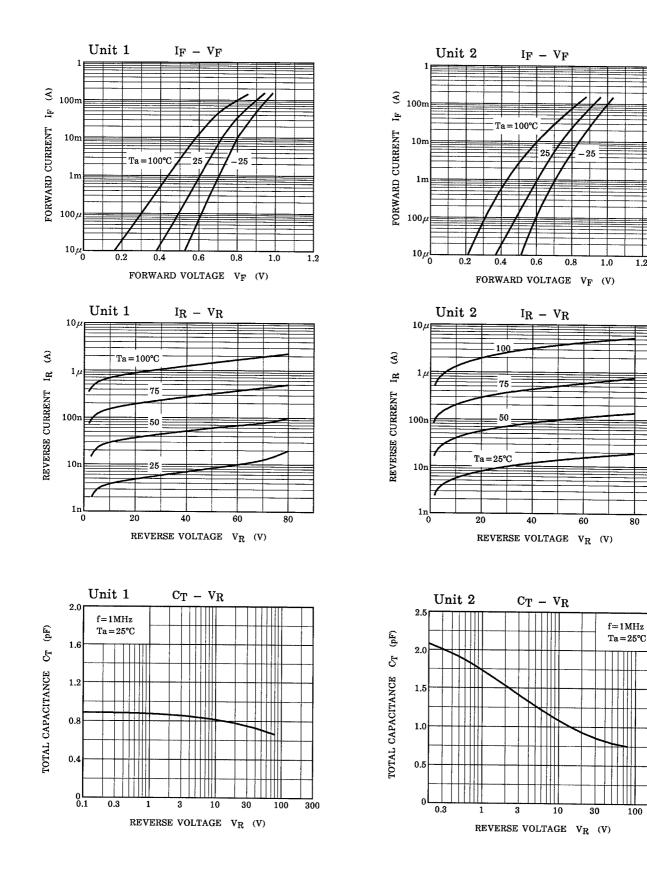
Unit 2 Electrical Characteristics (Q3, Q4, Common) (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Forward voltage	V _{F (1)}	_	I _F = 1mA		0.61			
	V _{F (2)}	_	I _F = 10mA		0.74		V	
	V _{F (3)}	-	I _F = 100mA	_	0.92	1.20		
Reverse current	I _{R (1)}	_	V _R = 30V		—	0.1	μΑ	
	I _{R (2)}	_	V _R = 80V		—	0.5		
Total capacitance	CT	_	V _R = 0, f = 1MHz		2.2	4.0	pF	
Reverse recovery time	t _{rr}	_	I _F = 10mA (fig.1)	_	1.6	4.0	ns	

TOSHIBA

1.2

80



100 300

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